

SANYO	No.4765	2SC4919
		NPN Epitaxial Planar Silicon Transistor
Muting Circuit Applications		

Features

- Very small-sized package permitting 2SC4919-applied sets to be made smaller and slimmer.
- Small output capacitance.
- Low collector-to-emitter saturation voltage.
- Small ON resistance.

Absolute Maximum Ratings at Ta = 25°C

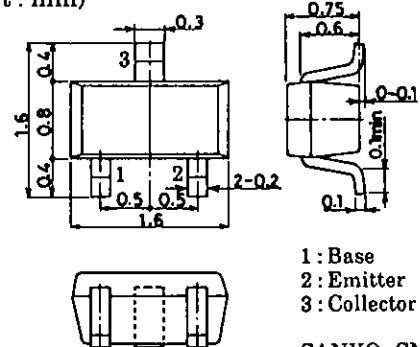
			unit
Collector-to-Base Voltage	V_{CBO}	25	V
Collector-to-Emitter Voltage	V_{CEO}	15	V
Emitter-to-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Collector Current (Pulse)	I_{CP}	200	mA
Base Current	I_B	20	mA
Collector Dissipation	P_C	150	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

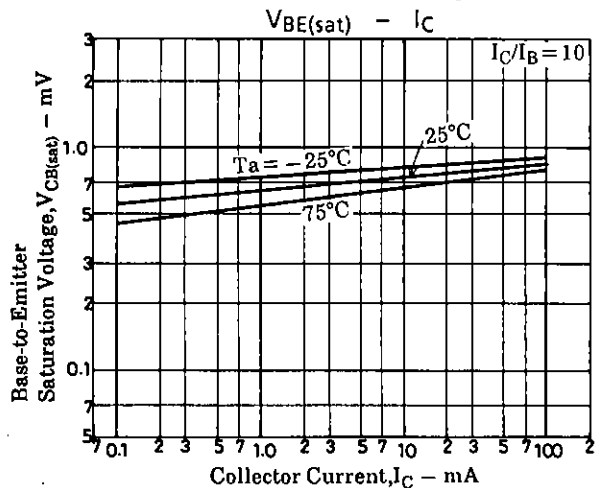
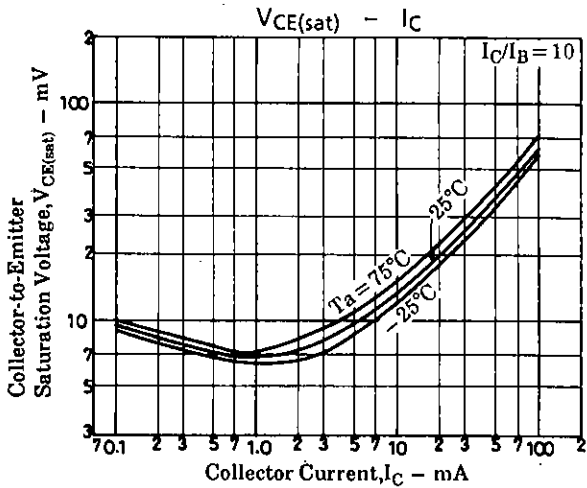
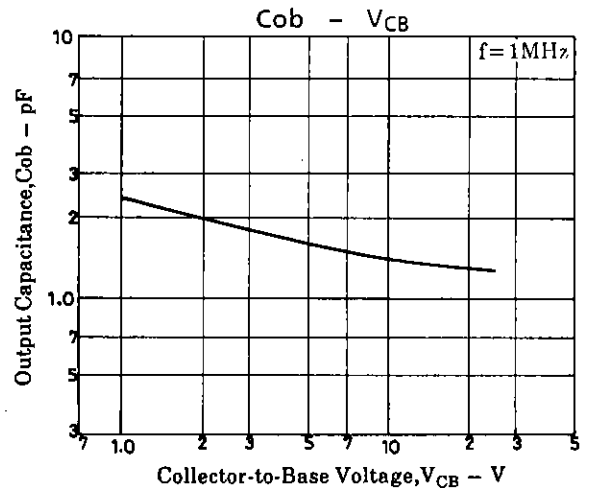
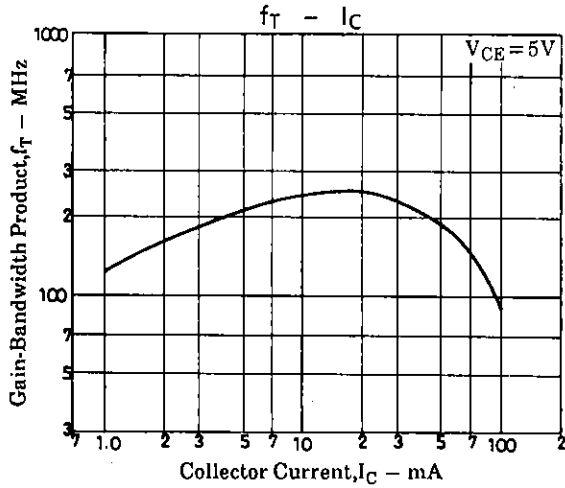
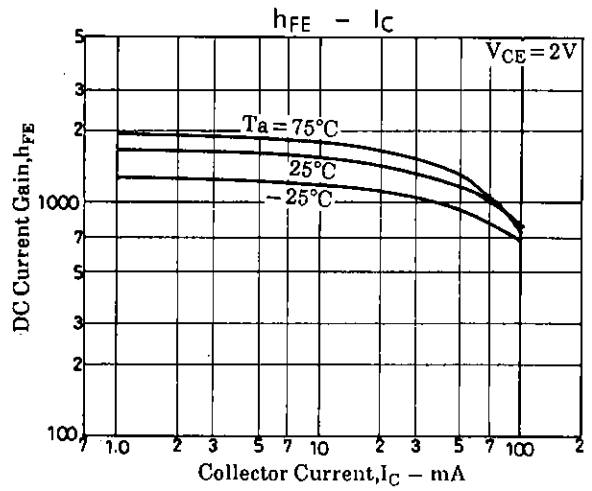
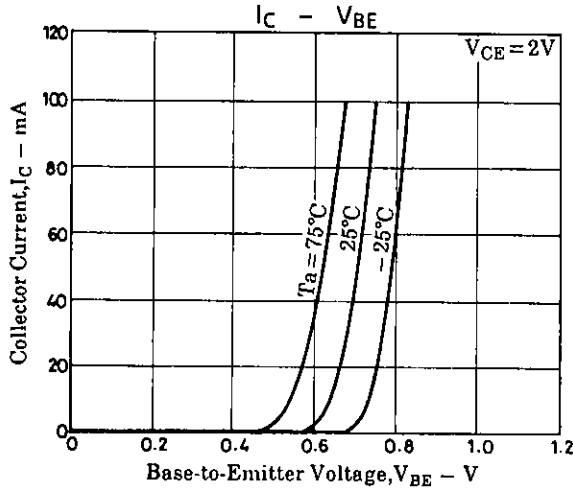
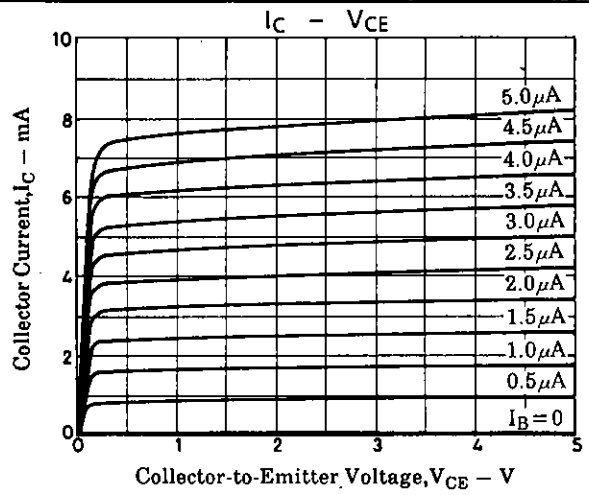
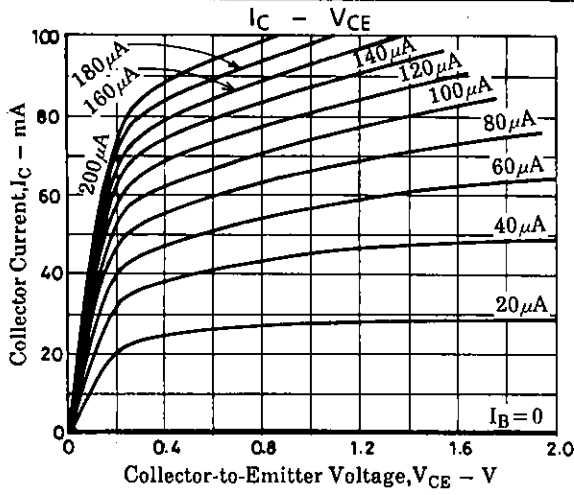
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 15V, I_E = 0$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4V, I_C = 0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 2V, I_C = 5mA$	800		3200	
Gain-Bandwidth Product	f_T	$V_{CE} = 5V, I_C = 10mA$		240		MHz
Output Capacitance	C_{ob}	$V_{CB} = 10V, f = 1MHz$		1.4		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$		14	30	mV
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 10mA, I_B = 1mA$		0.74	1.1	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	25			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, R_{BE} = \infty$	15			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	5			V
ON Resistance	R_{on}	$I_B = 3mA, f = 1MHz$		0.9		Ω

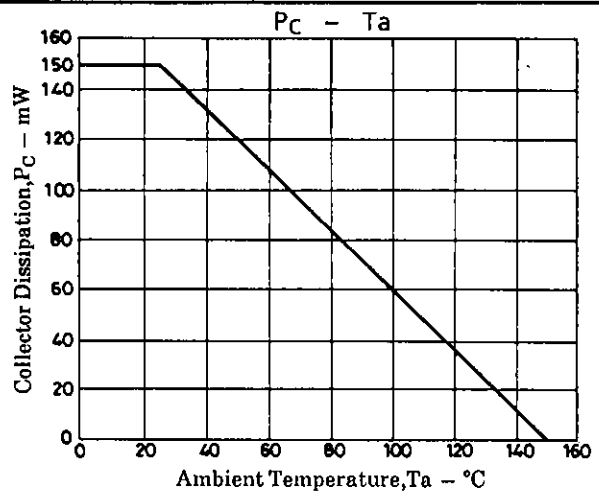
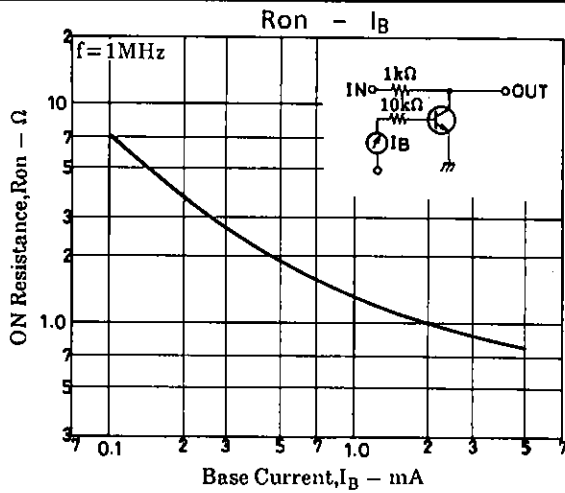
Marking : DA

Package Dimensions 2106A
(unit : mm)



SANYO : SMCP





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